

PLEASE AMEND THE CLAIMS AS FOLLOWS:

B1
19. (AMENDED) A cylindrical shaped, capacitor structure, featuring a cylindrical storage node structure comprised of an underlying cylindrical polysilicon shape and an overlying agglomerated metal silicide layer, comprising:

5 said cylindrical polysilicon shape comprised of a bottom polysilicon shape located on a first section of a top surface of an underlying planar, insulator layer, with said bottom polysilicon shape overlying and contacting a top surface of a plug structure which in turn is located
10 in an opening in said insulator layer, and with said cylindrical polysilicon shape comprised of vertical polysilicon shapes, located overlying second sections of said planar, insulator layer, with bottom portions of said vertical polysilicon shapes butting edges of
15 said bottom polysilicon shape;

 said agglomerated metal silicide layer, with a roughened top surface, located on exposed portions of said cylindrical polysilicon shape, featuring
20 agglomerated metal silicide on top surface of said bottom polysilicon shape, and on all surfaces of said vertical polysilicon shapes, resulting in said cylindrical shape storage node structure comprised of said agglomerated metal silicide layer on said cylindrical polysilicon shape;

B1
a capacitor dielectric layer located on the
exposed surfaces of said cylindrical shape storage node
structure; and

an upper electrode, covering said capacitor
5 dielectric layer.

B2
21. (AMENDED) The cylindrical shaped, capacitor structure of
Claim 19, wherein said agglomerated metal silicide layer
is selected from a group consisting of titanium
silicide, cobalt silicide, nickel silicide, and platinum
10 silicide.
